UTILITY PATENT APPLICATION OF CHRISTOPH NÖLSCHER ATTORNEY DOCKET No.: 0928.0016C

I claim:

1

1	1. A method for forming a structure element in a layer arranged on a water by a first
2	mask and a second trimming mask assigned to the first mask, comprising:
3	providing the wafer with the layer, the first mask, and the second trimming
4	mask;
5	applying a first photosensitive resist layer to the layer;
6	projecting a first mask structure pattern arranged on the first mask into the
7	first resist layer to form an exposed resist structure, the exposed resist structure at
8	least partly surrounding an unexposed resist element;
9	developing the first resist layer;
10	etching the layer with a transfer of the exposed resist structure into the layer, thereby
11	forming an elevated structure element in the layer below the unexposed resist element;
12	removing the first resist layer;
13	applying a second photosensitive resist layer to the layer;
14	projecting a second mask structure pattern arranged on the second
15	trimming mask into the second resist layer to form a second exposed resist
16	structure in the second resist layer, the second exposed resist structure at least
17	partly covering the elevated structure element in the layer;
18	developing the second resist layer; and
19	etching the layer with a transfer of the second exposed resist structure into the layer
20	and the elevated structure element.

2. The method as claimed in claim 1, wherein projecting the first mask

UTILITY PATENT APPLICATION OF CHRISTOPH NÖLSCHER ATTORNEY DOCKET NO.: 0928.0016C

2 structure pattern arranged on the first mask is carried out using an alternating or a chromeless 3 phase mask. 1 3. The method as claimed in claim 1, wherein projecting the first mask structure 2 pattern arranged on the first mask is carried out using a chrome or halftone phase mask with 3 oblique exposure. 1 The method as claimed in claim 1, wherein the elevated structure element is 2 formed in the layer, the elevated structure element including an electrically conductive 3 material. 1 The method as claimed in claim 1, wherein projecting the first mask structure 2 pattern arranged on the first mask forms a plurality of elevated metal interconnects, the metal 3 interconnects being arranged substantially parallel. 1 The method as claimed in claim 5, wherein, in etching of the layer with a transfer 2 of the second exposed resist structure into the layer, at least one of the elevated metal 3 interconnects is separated into at least two structure elements. 1 The method as claimed in claim 1, wherein projecting the first mask structure 2 pattern arranged on the first mask forms the elevated structure element in a partial region by a 3 phase jump and sets up on the first mask between two adjoining transparent regions on the 4 first mask, and etching of the layer with a transfer of the second exposed resist structure into 5 the layer removes the partial region.

UTILITY PATENT APPLICATION OF CHRISTOPH NÖLSCHER ATTORNEY DOCKET NO.: 0928.0016C

1	8. The method as claimed in claim 1, wherein, between removing the first resist
2	layer and applying the second photosensitive resist layer, an intermediate layer is deposited
3	and patterned lithographically.
1	9. The method as claimed in claim 8, wherein an electrically insulating material is
2	used as material of the intermediate layer.
1	10. The method as claimed in claim 8, wherein, in the lithographic patterning of the
2	intermediate layer, the elevated structure element is uncovered below the intermediate layer
3	by removal of a part of the intermediate layer.
1	11. The method as claimed in claim 10, wherein, in projecting the second mask
2	structure pattern arranged on the second trimming mask into the second resist layer, a third
3	exposed resist structure is exposed in the second resist layer, the third exposed resist structure
4	covering a region above the intermediate layer which has not been previously removed
5	during the lithographic patterning.
1	12. The method as claimed in claim 11, wherein the third exposed resist structure for
2	forming a contact hole, is transferred into the intermediate layer, the contact hole being filled
3	with an electrically conductive material in a further step.

UTILITY PATENT APPLICATION OF CHRISTOPH NÖLSCHER ATTORNEY DOCKET NO.: 0928.0016C

1	13. The method as claimed in claim 2, wherein projecting the first mask structure
2	pattern arranged on the first mask forms a plurality of elevated metal interconnects, the metal
3	interconnects being arranged substantially parallel.
1	14. The method as claimed in claim 3, wherein projecting the first mask structure
2	pattern arranged on the first mask forms a plurality of elevated metal interconnects, the metal
3	interconnects being arranged substantially parallel.
1	15. The method as claimed in claim 13, wherein, in etching of the layer with a
2	transfer of the second exposed resist structure into the layer, at least one of the elevated metal
3	interconnects is separated into at least two structure elements.
1	16. The method as claimed in claim 14, wherein, in etching of the layer with a
2	transfer of the second exposed resist structure into the layer, at least one of the elevated metal
3	interconnects is separated into at least two structure elements.